Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

Applications

- Power management in half bridge and inverters
- DC-DC Converter
- Load Switch

General Description

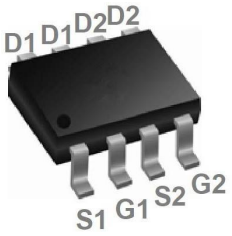
The XR4606C is the highest performance trench N-ch and P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

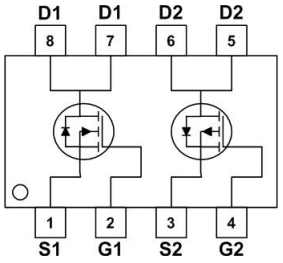
The XR4606C meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Product Summary

BVDSS	RDSON	ID
20V	45mΩ	3A
-20V	80mΩ	- 3A

SOP-8 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	20	-20	V
V_{GS}	Gate-Source Voltage	±12	±12	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	3.0	-3	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	2.0	-2	A
I_{DM}	Pulsed Drain Current[2]	12	-10	A
P_D@T_C=25℃	Total Power Dissipation[4]	2.5	2.08	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	105	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	50	℃/W

Electrical Characteristics (T_J=25℃unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250μA	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =20V, V_{GS} = 0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V,V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	0.4	0.7	1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS} =4.5V, I_D =3A	-	45	55	mΩ
		V_{GS} =2.5V, I_D =2A	-	62	85	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} =10V, V_{GS} =0V, f = 1.0MHz	-	184	-	pF
C_{oss}	Output Capacitance		-	38	-	pF
C_{rss}	Reverse Transfer Capacitance		-	28	-	pF
Q_g	Total Gate Charge	V_{DS} =10V, I_D =3A, V_{GS} =4.5V	-	2.7	-	nC
Q_{gs}	Gate-Source Charge		-	0.4	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	0.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V,I_D=3A, R_{GEN}=3Ω, V_{GS} =4.5V	-	8	-	ns
t_r	Turn-on Rise Time		-	27	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	26	-	ns
t_f	Turn-off Fall Time		-	33	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	3	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S=3A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Electrical Characteristics (T_C=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D= -250μA	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -20V, V_{GS} = 0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-0.4	-0.7	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS} =-4.5V, I_D =-2.5A	-	80	104	mΩ
		V_{GS} =-2.5V, I_D =-1.5A	-	110	154	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz	-	248	-	pF
C_{oss}	Output Capacitance		-	42	-	pF
C_{rss}	Reverse Transfer Capacitance		-	31	-	pF
Q_g	Total Gate Charge	V_{DS} = -10V, I_D = -2.5A, V_{GS} = -4.5V	-	2.9	-	nC
Q_{gs}	Gate-Source Charge		-	0.45	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	0.75	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = -10V, R_L=5Ω, R_{GEN}=3Ω,V_{GS}=-4.5V,	-	9.8	-	ns
t_r	Turn-on Rise Time		-	4.9	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	20.5	-	ns
t_f	Turn-off Fall Time		-	7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-3.0	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-10	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = -2.5A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

N-Channel Typical Characteristics

Figure1: Output Characteristics

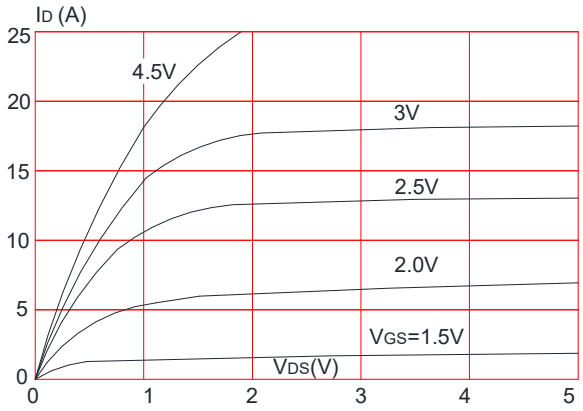


Figure 2: Typical Transfer Characteristics

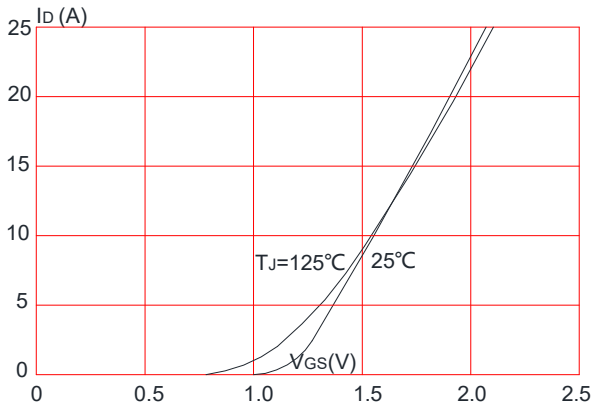


Figure 3: On-resistance vs. Drain Current

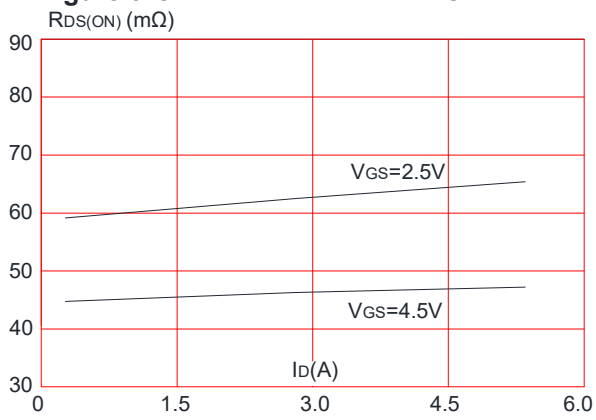


Figure 4: Body Diode Characteristics

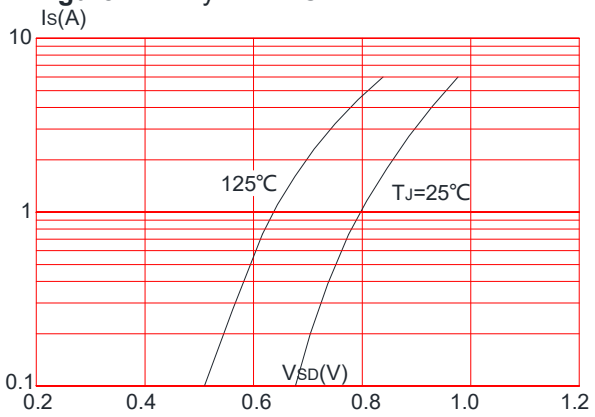


Figure 5: Gate Charge Characteristics

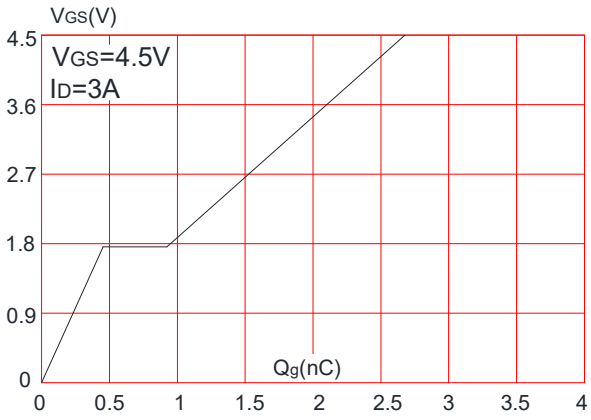
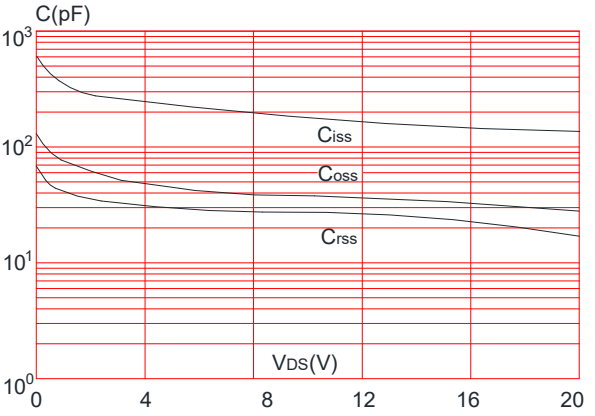


Figure 6: Capacitance Characteristics



N-Channel Typical Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

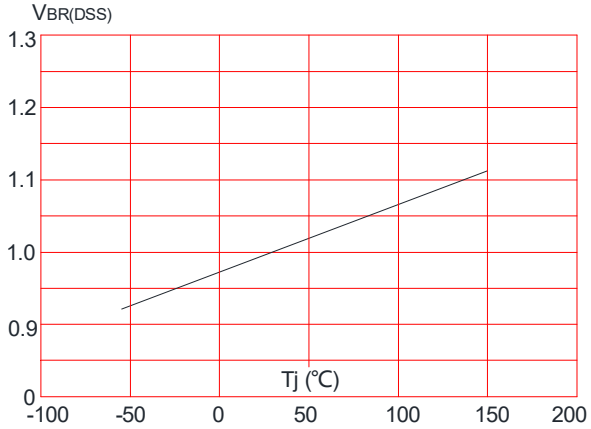


Figure 8: Normalized on Resistance vs. Junction Temperature

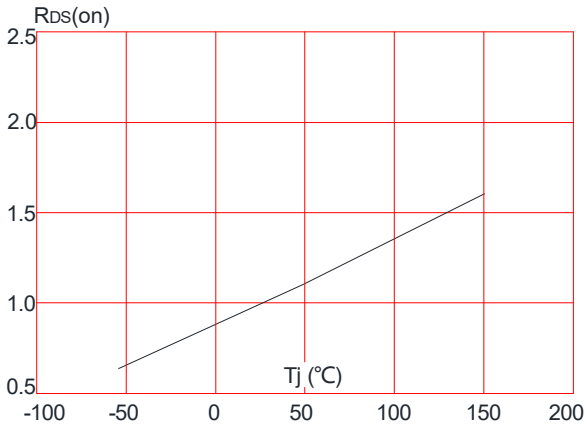


Figure 9: Maximum Safe Operating Area

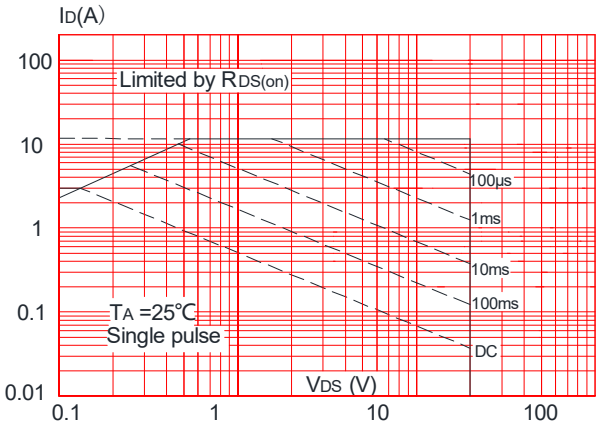


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

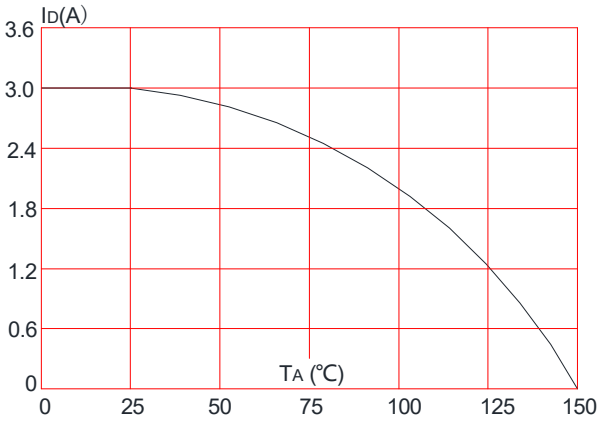
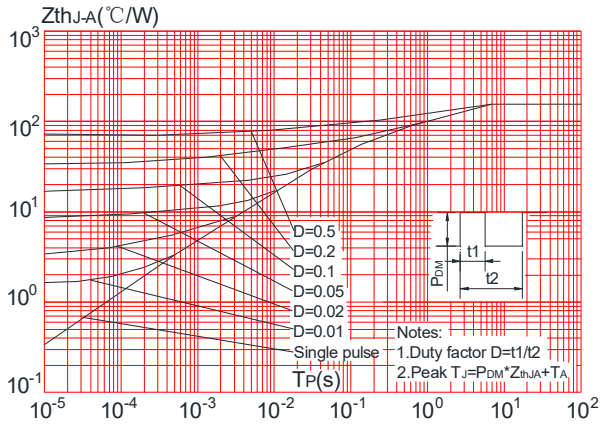


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



P-Channel Typical Characteristics

Figure1: Output Characteristics

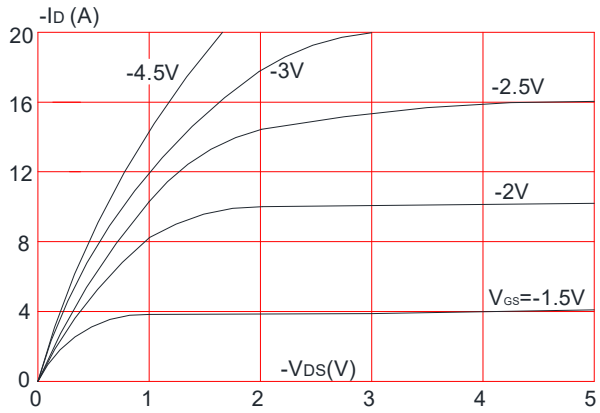


Figure 2: Typical Transfer Characteristics

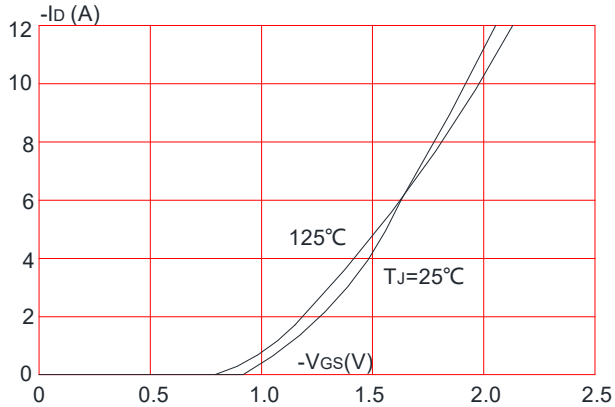


Figure 3: On-resistance vs. Drain Current

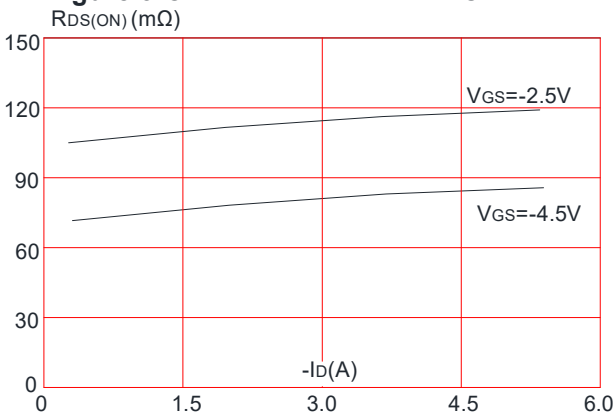


Figure 4: Body Diode Characteristics

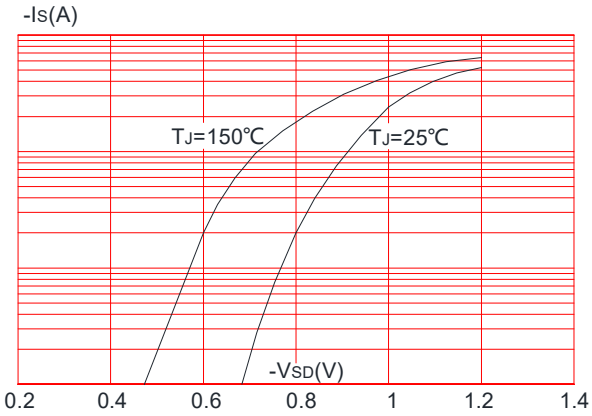


Figure 5: Gate Charge Characteristics

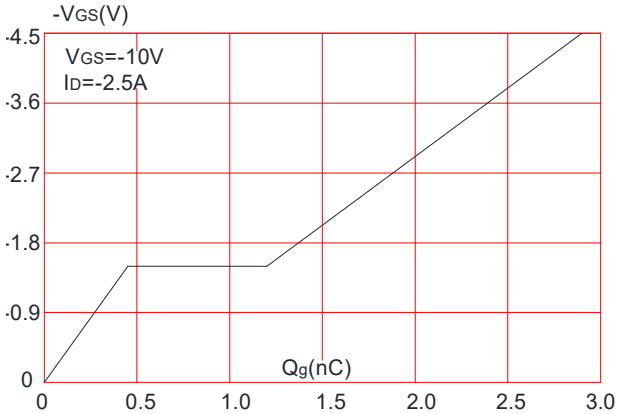
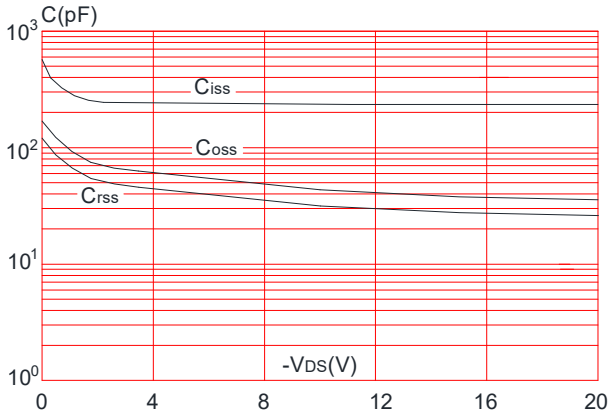


Figure 6: Capacitance Characteristics



P-Channel Typical Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

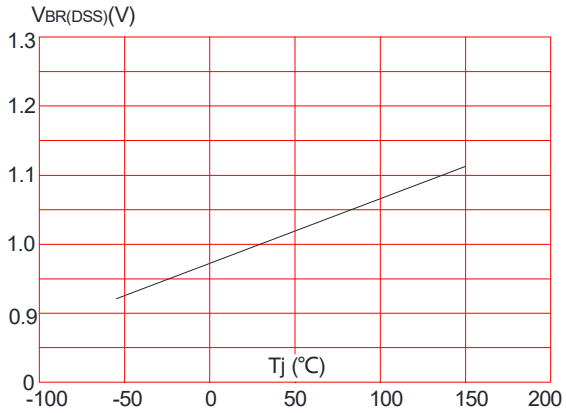


Figure 8: Normalized on Resistance vs. Junction Temperature

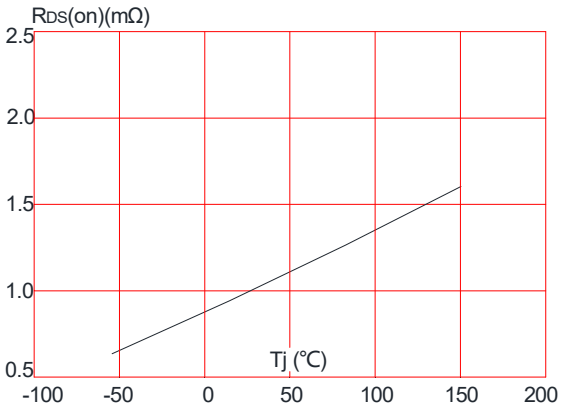


Figure 9: Maximum Safe Operating Area

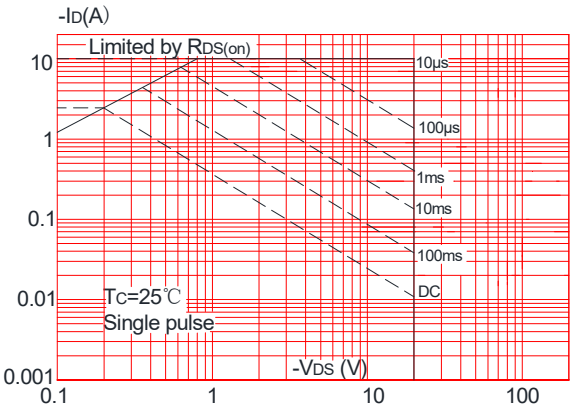


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

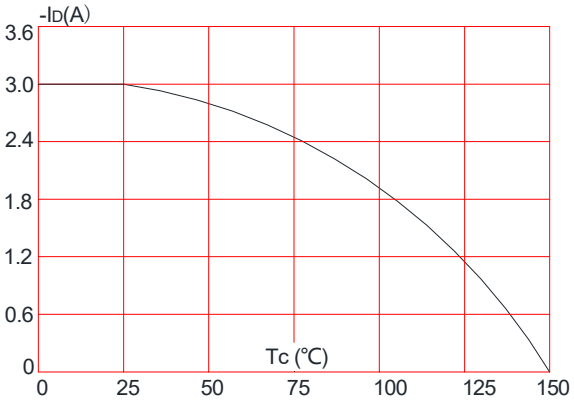
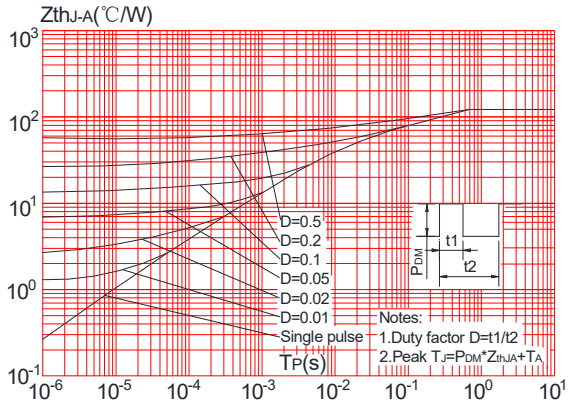
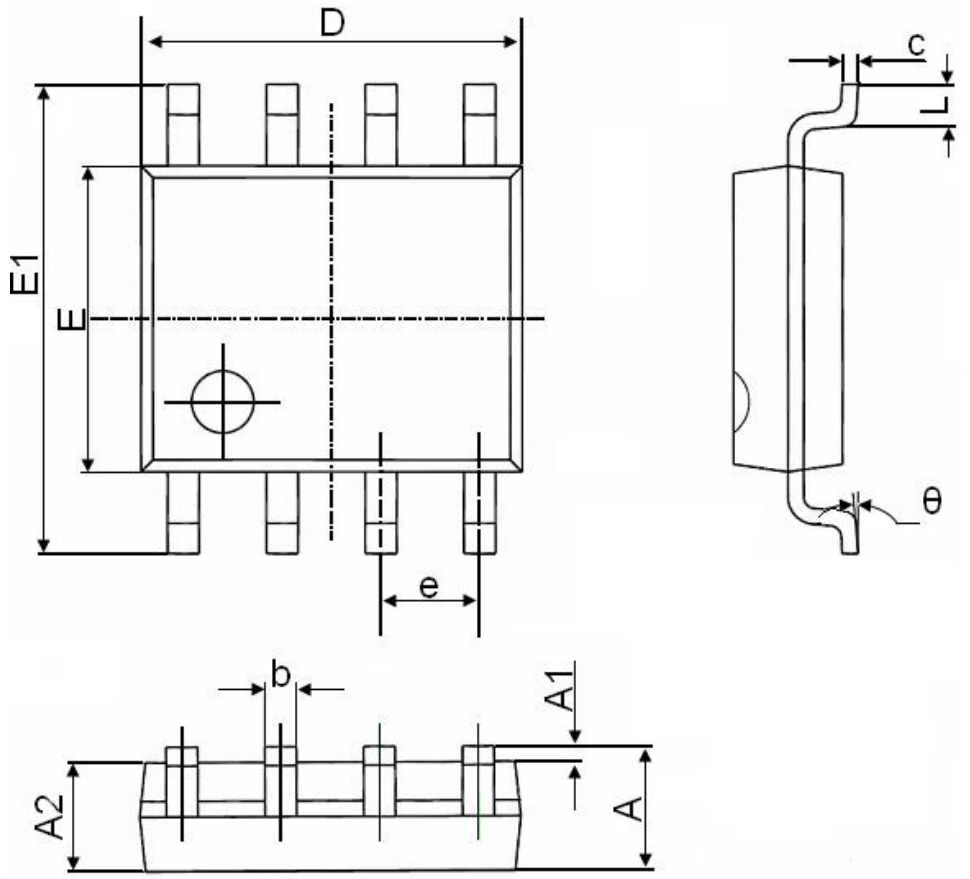


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°